

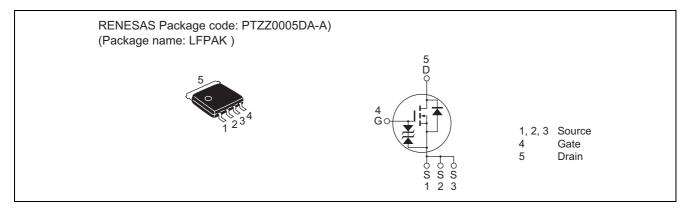
HAT2174H Silicon N Channel Power MOS FET Power Switching

REJ03G0041-0400 Rev.4.00 Dec 11, 2006

Features

- Capable of 8 V gate drive
- Low drive current
- High density mounting
- Low on-resistance
- $R_{DS(on)} = 21 \text{ m}\Omega \text{ typ.} (at V_{GS} = 10 \text{ V})$

Outline



Absolute Maximum Ratings

			(Ta = 25°C)
Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	100	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	20	A
Drain peak current	Note1 I _{D(pulse)}	80	A
Body-drain diode reverse drain current	I _{DR}	20	A
Avalanche current	I _{AP} Note 2	20	A
Avalanche energy	E _{AR} Note 2	40	mJ
Channel dissipation	Pch Note3	20	W
Channel to Case Thermal Resistance	θch-C	6.25	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. Value at Tch = 25°C, Rg \ge 50 Ω

3. Tc = 25°C



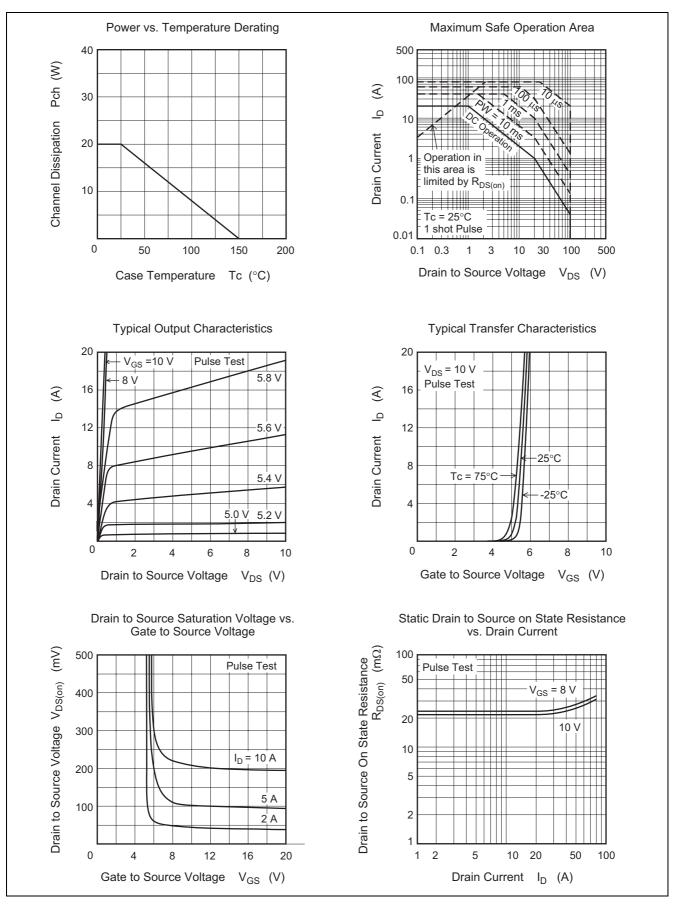
Electrical Characteristics

						$(Ta = 25^{\circ}C)$	
Item	Symbol	Min	Тур	Max	Unit	Test Conditions	
Drain to source breakdown voltage	V _{(BR)DSS}	100			V	$I_D = 10 \text{ mA}, V_{GS} = 0$	
Gate to source breakdown voltage	V _{(BR)GSS}	±20	_	_	V	$I_{G} = \pm 100 \ \mu A, \ V_{DS} = 0$	
Gate to source leak current	I _{GSS}	_		±10	μΑ	$V_{GS} = \pm 16 V, V_{DS} = 0$	
Zero gate voltage drain current	I _{DSS}	_		1	μΑ	$V_{DS} = 100 V, V_{GS} = 0$	
Gate to source cutoff voltage	V _{GS(off)}	4.0		6.0	V	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{mA}$	
Static drain to source on state	R _{DS(on)}	_	21	27	mΩ	$I_D = 10 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$	
resistance	R _{DS(on)}	_	22	30	mΩ	$I_D = 10 \text{ A}, V_{GS} = 8 \text{ V}^{\text{Note4}}$	
Forward transfer admittance	y _{fs}	21	35	_	S	$I_D = 10 \text{ A}, V_{DS} = 10 \text{ V}^{Note4}$	
Input capacitance	Ciss	_	2280	_	pF	V _{DS} = 10 V,V _{GS} = 0, f = 1 MHz	
Output capacitance	Coss	_	285	_	pF		
Reverse transfer capacitance	Crss		100		pF		
Gate Resistance	Rg		0.5		Ω		
Total gate charge	Qg		33.5		nC	$V_{DD} = 50 \text{ V}, V_{GS} = 10 \text{ V},$	
Gate to source charge	Qgs		12.4		nC	I _D = 20 A	
Gate to drain charge	Qgd	_	8.4	_	nC	1	
Turn-on delay time	t _{d(on)}		18		ns	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 10 \text{ A},$	
Rise time	tr	_	13	_	ns	$V_{\text{DD}} \cong 30 \text{ V}, \text{ R}_{\text{L}} = 3 \Omega,$ Rg = 4.7 Ω	
Turn-off delay time	t _{d(off)}	_	31	_	ns		
Fall time	t _f		5.5		ns		
Body–drain diode forward voltage	V _{DF}	_	0.84	1.10	V	$IF = 20 A, V_{GS} = 0^{Note4}$	
Body-drain diode reverse recovery	t _{rr}		50	_	ns	$IF = 20 A, V_{GS} = 0$	
time						di _F / dt = 100 A/ μs	

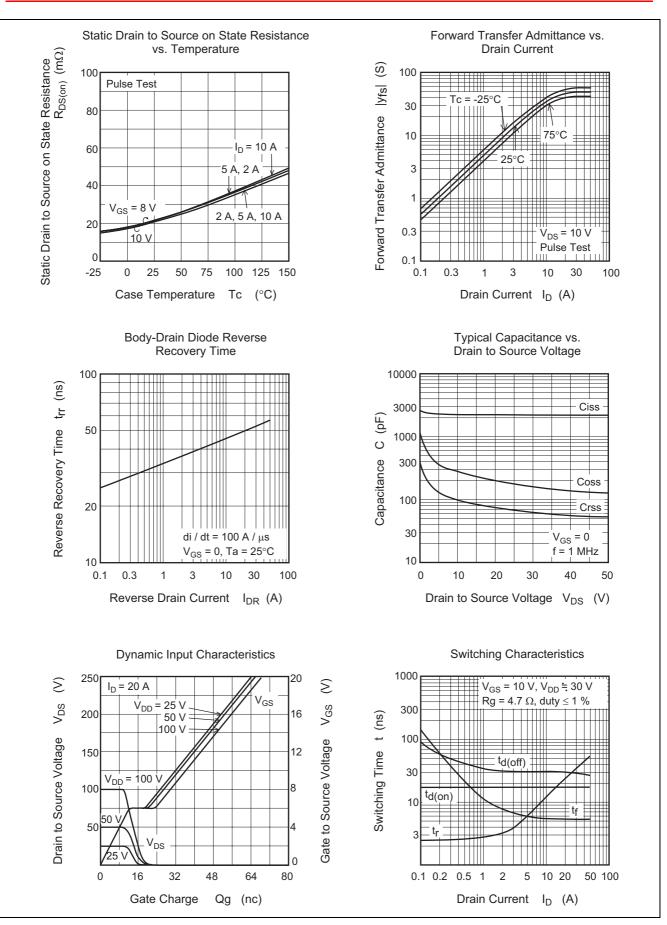
Notes: 4. Pulse test



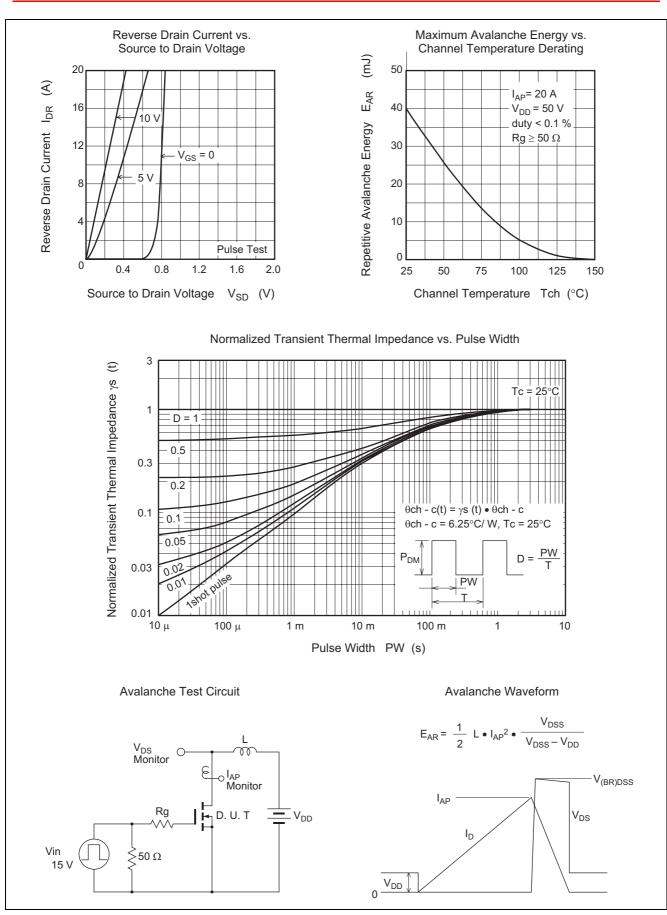
Main Characteristics



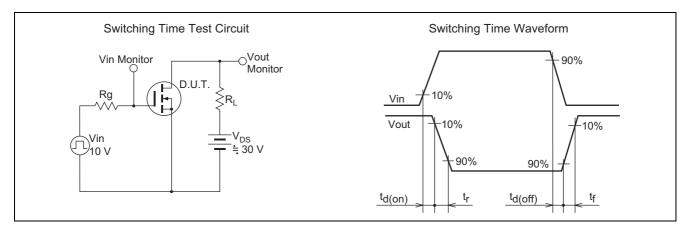






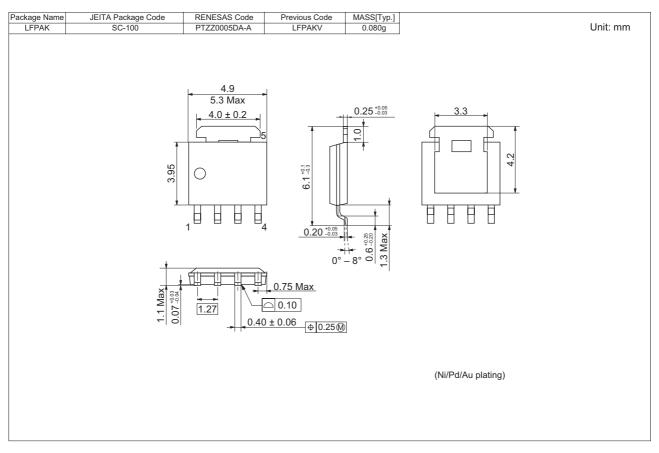








Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
HAT2174H-EL-E	2500 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.



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